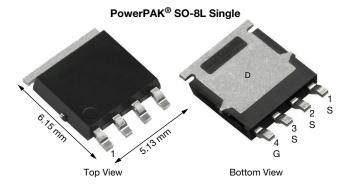
# SQJ479EP



**Vishay Siliconix** 

# Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-80
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = -10 V	0.033
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = -4.5 V	0.044
I <sub>D</sub> (A)	-32
Configuration	Single
Package	PowerPAK SO-8L



### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

G C

S

P-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	-80	N	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1-	-32		
	T <sub>C</sub> = 125 °C	ID	-18		
Continuous Source Current (Diode Conduction) a		IS	-60	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-100		
Single Pulse Avalanche Current		I <sub>AS</sub>	-40		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	80	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	68	14/	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	22	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	68	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.2	C/W

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•				<b>I</b>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μΑ	-80	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{GS}$ , $I_D$ = -250 $\mu$ A	-1.5	-2.0	-2.5	v
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -80 V	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -80 V, T <sub>J</sub> = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -80 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge -5 V$	-30	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A	-	0.0275	0.0330	
Drain Source On State Desistence a	Р	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 125 °C	-	-	0.0544	0
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -10 A, T <sub>J</sub> = 175 °C	-	-	0.0670	Ω
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A	-	0.0360	0.0440	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = -10 A	-	25	-	S
Dynamic <sup>b</sup>	·	-					
Input Capacitance	C <sub>iss</sub>			-	3290	4500	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -25 V, f = 1 MHz	-	320	450	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	215	300	
Total Gate Charge <sup>c</sup>	Qg			-	90	150	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -40 \text{ V}, I_D = -10 \text{ A}$	-	11	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	24	-	
Gate Resistance	Rg		f = 1 MHz	0.50	1.16	1.80	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	15	25	
Rise Time <sup>c</sup>	t <sub>r</sub>		-40 V, R <sub>I</sub> = 10 Ω	-	5	10	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -4 Å, '	$V_{\text{GEN}} = -10$ V, $R_{\text{g}} = 1 \Omega$	-	50	80	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	6	10	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-100	Α
					-		V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



8

 $V_{GS}$ 10 V

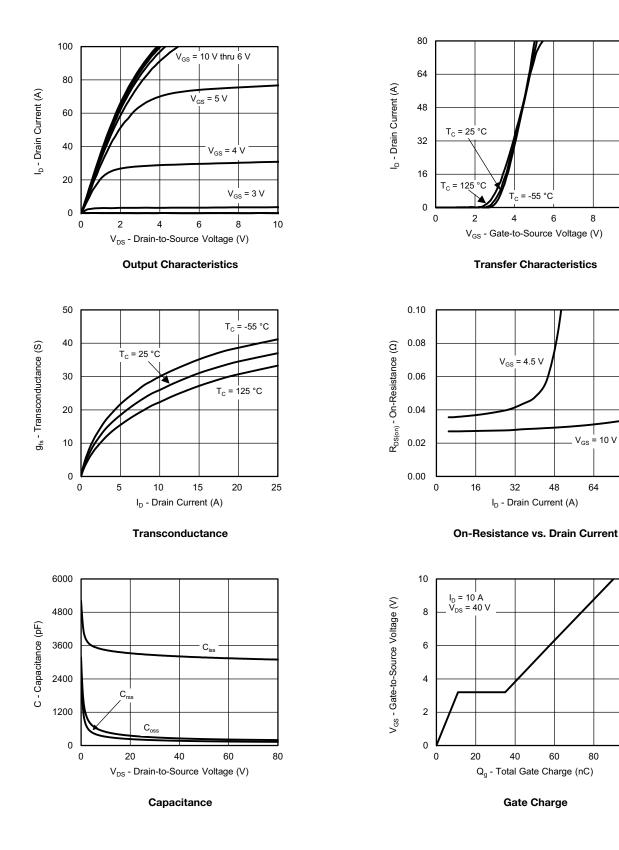
64

80

80

10

## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





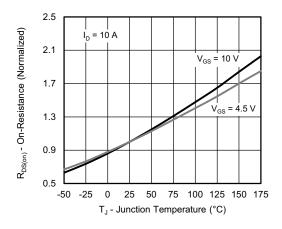
3

100

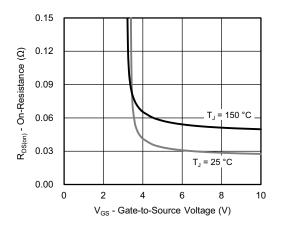
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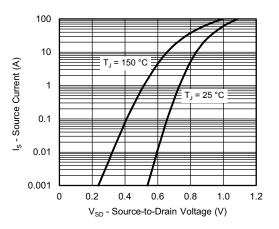
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



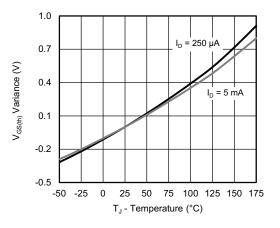
**On-Resistance vs. Junction Temperature** 

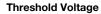


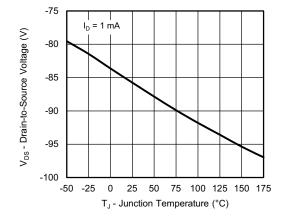
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







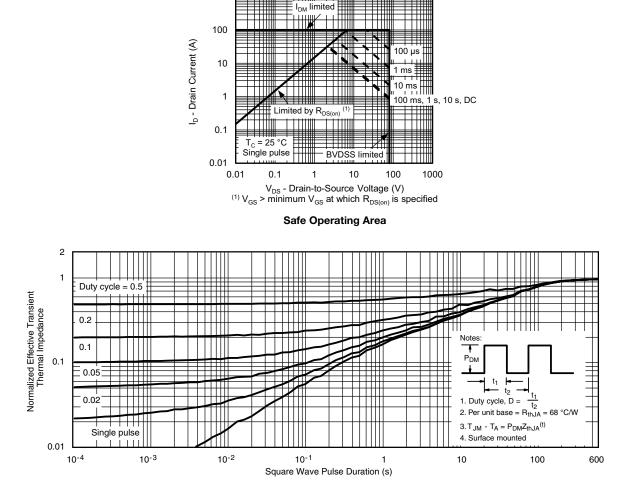
**Drain-Source Breakdown vs. Junction Temperature** 

4



### THERMAL RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

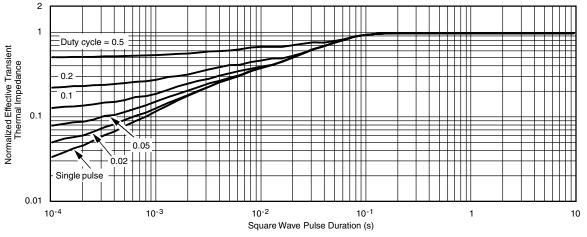
1000

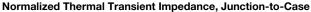


Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)





#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75129.









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# **Package Information**



Vishay Siliconix

DIM.	MILLIMETERS			INCHES				
	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К	0.51				0.020			
W	0.23			0.009				
W1	0.41			0.016				
W2	2.82			0.111				
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK<sup>®</sup> SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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